#### Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

Except below description page
 "Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

Doc No. TT4-EA-12100

Revision. 2

## **Panasonic**

MOS FET

#### MTMC8E2A0LBF

## MTMC8E2A0LBF

### Gate Resistor installed Dual N-Channel MOS Typ

For lithium-ion secondary battery protection circuit

#### ■ Features

- Low drain-source On-state Resistance RDS(on) typ. = 15 m $\Omega$  (VGS =4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 4B

#### ■ Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

	Unit: mm				
2. 9	2. 9				
***************************************	0.3 0.16				
	3 4 (0.81)				
0. 65					
1. Source	e 5. Drain				
2. Gate	6. Drain				
3. Source	e 7. Drain				
4. Gate	8. Drain				
Panasonic	WMini8-F1				
JEITA	SC-115				
Code	_				

#### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter		Symbol	Rating	Unit	
	Drain-source Voltage	VDS	20	V	
	Gate-source Voltage	VGS	±12	V	
	Drain current	ID	7.0	Α	
	Peak drain current	IDp	42	Α	
Overall		PD1 *1	1.0		
	Total power dissipation	PD2 *1,2	1.2	W	
		PD3 *3	0.4		
	Channel temperature	Tch	150	°C	
	Operating ambient temperature	Topr	-40 to + 85	°C	
	Storage temperature	Tstg	-55 to +150	°C	

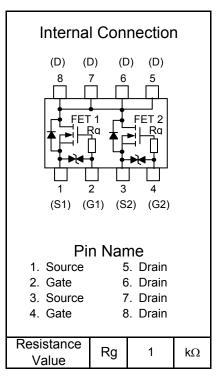
- Note) \*1 Glass epoxy board: 25.4 mm × 25.4 mm × 0.8 mm Copper foil of the drain portion should have a area of 300 mm<sup>2</sup> or more PD absolute maximum rating without a heat shink: 400 mW
  - \*2 t = 10 s

Established: 2010-01-06

: 2013-09-02

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\*3 Stand-alone (without the board)



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## **Panasonic**

### MOS FET MTMC8E2A0LBF

#### ■ Electrical Characteristics Ta = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = 1.0 mA, VGS = 0	20	<u> </u>		V
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA
Gate-source cutoff current	IGSS	VGS = ±8.0 V, VDS = 0			±10	μA
Gate threshold voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.40	0.85	1.30	V
	RDS(ON)1	ID = 2.0 A, VGS = 4.5 V		15	21	mΩ
Drain-source ON resistance	RDS(ON)2	ID = 2.0 A, VGS = 3.7 V		18	25	mΩ
	RDS(ON)3	ID = 2.0 A, VGS = 2.5 V		22	33	mΩ
Forward transfer admittance	Yfs	ID = 1.0 A, VDS = 10 V	3.0			S
Short-circuit input capacitance (Common source)	Ciss			1450		pF
Short-circuit output capacitance (Common source)	Coss	VDS = 10 V, VGS = 0, f = 1 MHz		100		pF
Reverse transfer capacitance (Common source)	Crss			90		pF
Turn-on delay time *1	td(on)	VDD = 10 V, VGS = 0 V to 4 V		0.33		μs
Rise time *1	tr	ID = 1.0 A		0.70		μs
Turn-off delay time *1	td(off)	VDD = 10 V, VGS = 4 V to 0 V		4.0		μs
Fall time *1	tf	ID = 1.0 A		2.0		μs

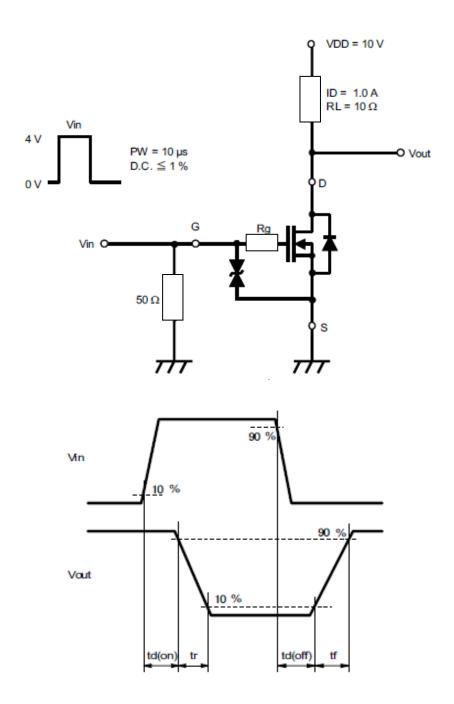
Note) 1 Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

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<sup>2. \*1</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

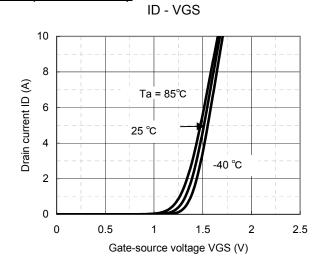


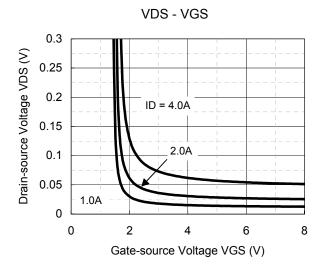
MOS FET

### MTMC8E2A0LBF

## Technical Data (reference)

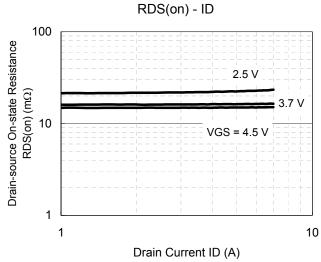
ID - VDS 6 /GS = 4.5 V 5 Drain Current ID (A) 2.5 V 3 2.0 V 2 1.5 V 0 0 0.1 0.2 0.3 Drain-source Voltage VDS (V)





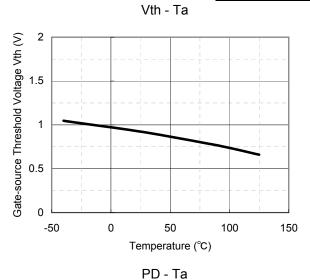
Established: 2010-01-06

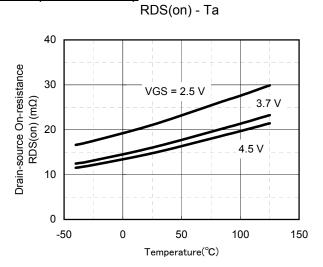
Revised

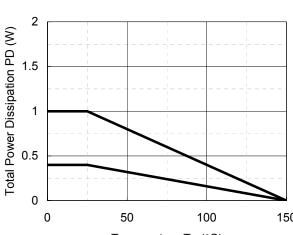


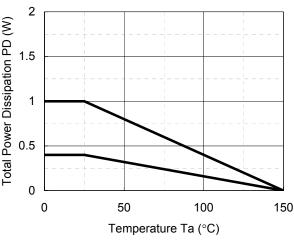
MOS FET MTMC8E2A0LBF

## Technical Data (reference)

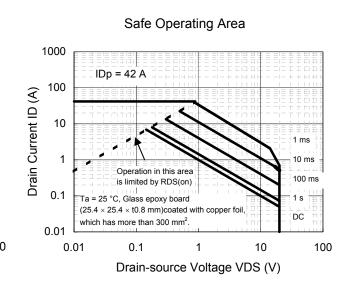








Rth - tsw



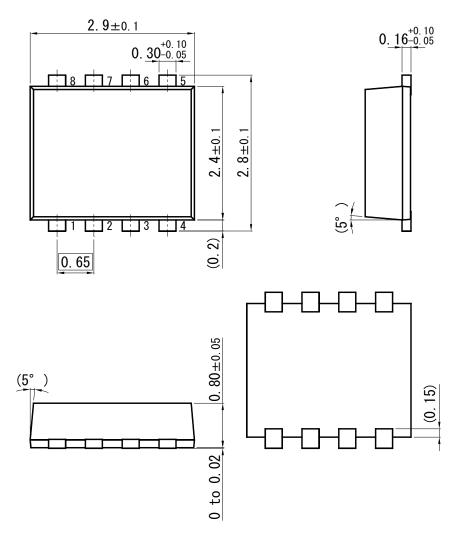
1000 Thermal Resistance Rth (°C/W) 100 10 0.01 0.1 100 1000 1 10 Pulse Width tsw (s)

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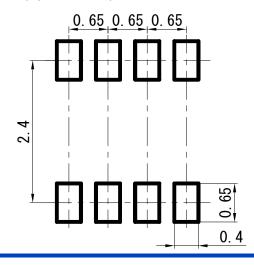
MOS FET MTMC8E2A0LBF

WMini8-F1

Unit: mm



Land Pattern (Reference) (Unit: mm)



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